

Amendments to the Specification:

Please replace the paragraph beginning at page 13, line 3, with the following amended paragraph:

Next, a first interlayer insulating film 46 is formed in order to protect the thin film integrated circuit elements. Although a silicon nitride film is formed by plasma CVD here, the first interlayer insulating film 46 is not limited to the film. Further, a second interlayer insulating film 47 is formed for planarization of unevenness due to the thin film integrated circuits. A heat-resistant organic resin such as siloxane, or an organic resin such as polyimide, acrylic, and polyamide, ~~or siloxane~~ can be used to form the second interlayer insulating film 46 by spin coating, dip coating, spraying, or a droplet discharge method. Alternatively, an inorganic material such as PSG (phosphosilicate glass), BPSG (borophosphosilicate glass), or alumina may be used.